

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

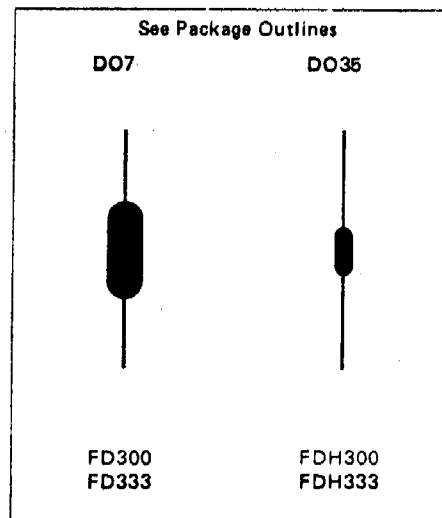
TELEPHONE: (201) 376-2922
(212) 227-6005
FAX: (201) 376-8960

FD300 • FD333 • FDH300 • FDH333

HIGH CONDUCTANCE LOW LEAKAGE
DIFFUSED SILICON PLANAR DIODES

ABSOLUTE MAXIMUM RATINGS

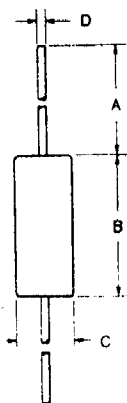
Maximum Temperatures			
Storage Temperature			-65°C to +200°C
Operating Temperature			175°C
Maximum Power Dissipation (Notes 2 & 3)		FD300, FD333	FDH300, FDH333
Total Dissipation at 25°C Ambient Temperature		400 mW	500 mW
Linear Derating Factor		2.67 mW/°C	3.33 mW/°C
Maximum Voltages and Currents			
WIV	Working Inverse Voltage	125 V	125 V
I _O	Average Rectified Current	150 mA	200 mA
I _F	Forward Current Steady State	375 mA	500 mA
I _F	Recurrent Peak Forward Current	450 mA	600 mA
I _F (surge)	Peak Forward Surge Current		
	Pulse Width = 1.0 s	500 mA	1000 mA
	Pulse Width = 1.0 μs	4000 mA	4000 mA



ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	FD300, FDH300 MIN. MAX.	FD333, FDH333 MIN. MAX.	UNITS	TEST CONDITIONS
V _F	Forward Voltage		0.9 1.15	V	I _F = 300 mA
			0.88 1.08	V	I _F = 250 mA
		1.0	0.87 1.05	V	I _F = 200 mA
			0.86 0.97	V	I _F = 150 mA
		0.92	0.83 0.94	V	I _F = 100 mA
		0.88	0.80 0.89	V	I _F = 50 mA
		0.8		V	I _F = 10 mA
		0.75		V	I _F = 5.0 mA
		0.68		V	I _F = 1.0 mA
I _R	Reverse Current	1.0	3.0	nA	V _R = -125 V
		3.0		μA	V _R = -125 V, T _A = 150°C
			500	nA	V _R = -125 V, T _A = 100°C
C	Capacitance		6.0	pF	V _R = 0
BV	Breakdown Voltage	150	150	V	I _R = 100 μA

DO35



DIM.	INCHES			MILLIMETERS		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.0			25.40		
B			.180			4.57
C			.075			1.91
D		.020			0.508	



Quality Semi-Conductors